

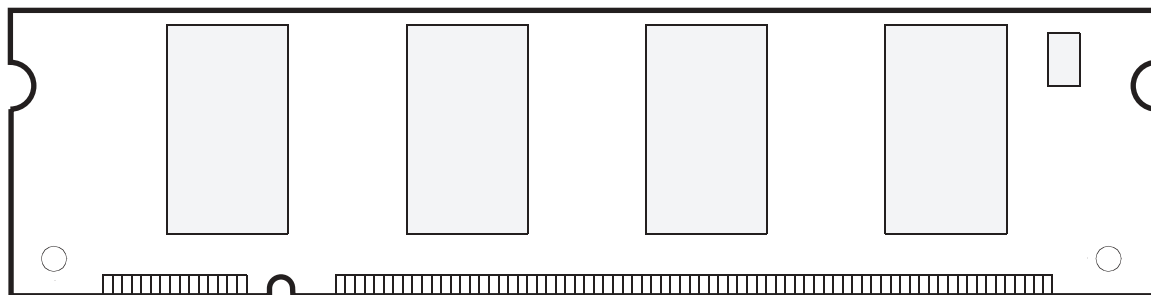
**Features**

- JEDEC 200 Pin DDR Unbuffered Small-Outline, Dual In-Line memory module (SODIMM); 33,554,432 x 64 bit organization.
- Utilizes High Performance 32M x 8 DDR SDRAM in TSOPII-66 Packages
- Single +2.5V ( $\pm 0.2V$ ) Power Supply
- Single +2.6V ( $\pm 0.1V$ ) Power Supply for DDR400
- Programmable CAS Latency, Burst Length, and Wrap Sequence (Sequential & Interleave)
- Auto Refresh (CBR) and Self Refresh
- All Inputs, Outputs are SSTL-2 Compatible
- 8192 Refresh Cycles every 64 ms
- Serial Presence Detect (SPD)

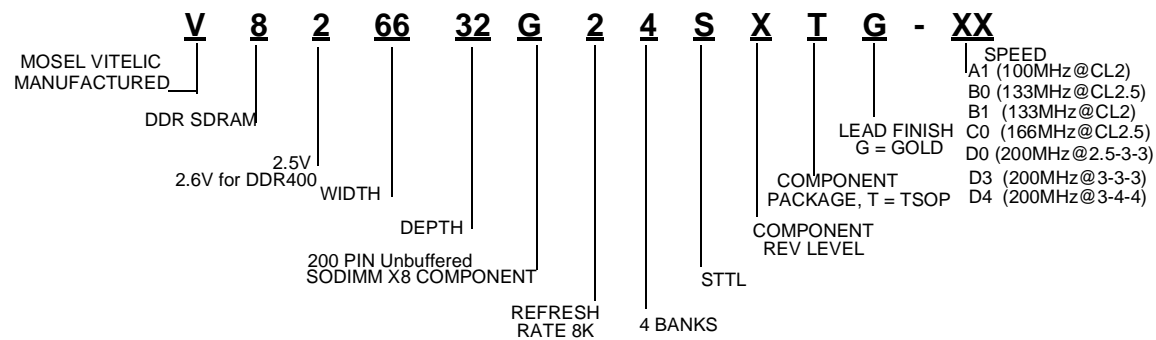
**Description**

The V826632G24S memory module is organized 33,554,432 x 64 bits in a 200 pin memory module. The 32M x 64 memory module uses 8 Mosel-Vitellic 32M x 8 DDR SDRAM. The x64 modules are ideal for use in high performance computer systems where increased memory density and fast access times are required.

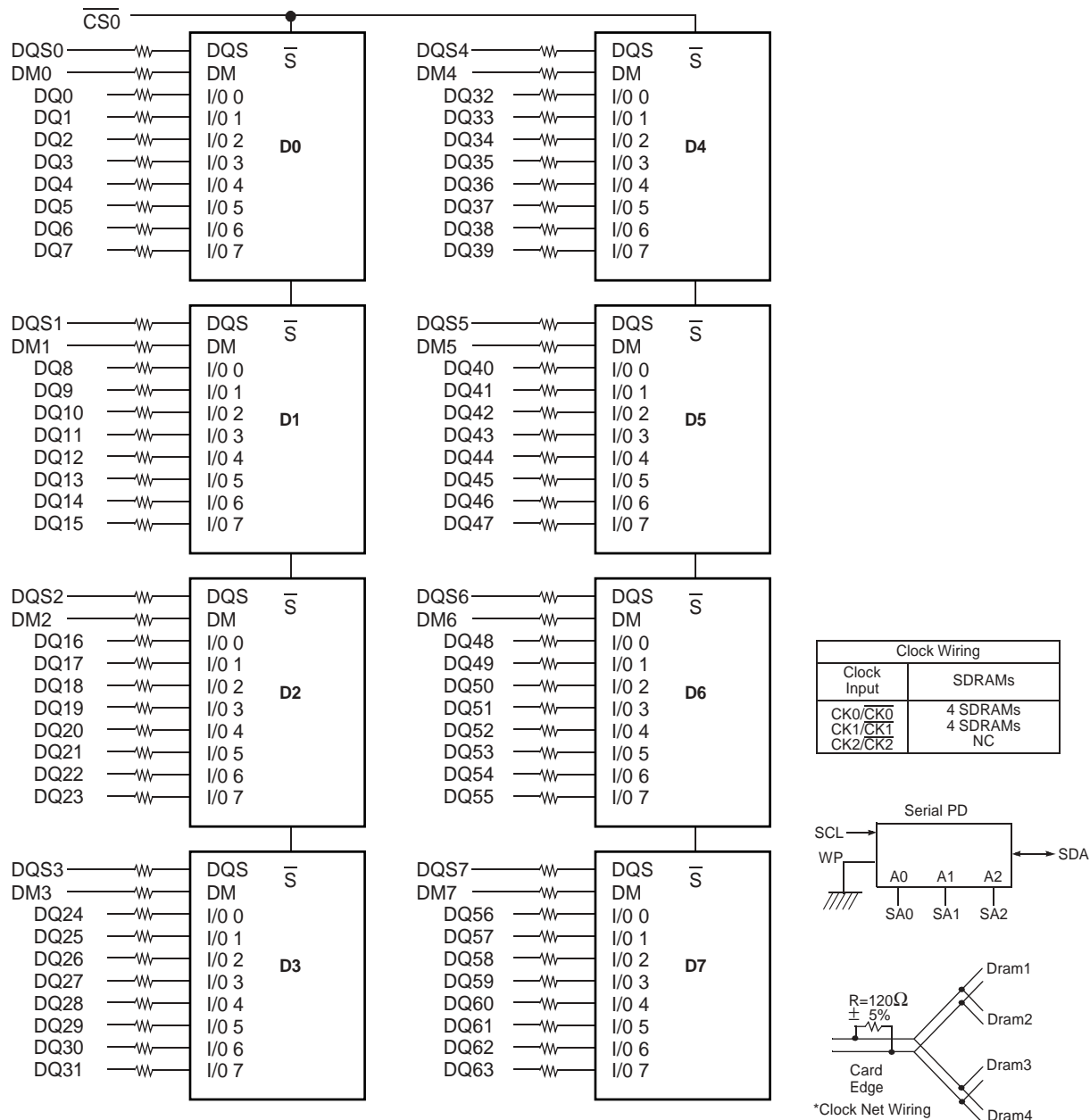
	Module Speed	D4	D3	D0	C0	B1	B0	A1	Units
$t_{CK}$	Clock Frequency (max.)	200 (PC400C)	200 (PC400B)	200 (PC400A)	166 (PC333)	143 (PC266A)	133 (PC266B)	125 (PC200)	MHz
$t_{AC}$	Clock Cycle Time CAS Latency = 2	7.5	7.5	7.5	7.5	7.5	10	10	ns
$t_{AC}$	Clock Cycle Time CAS Latency = 2.5	6	6	5	6	7	7.5	8	ns
$t_{AC}$	Clock Cycle Time CAS Latency = 3	5	5	5	-	-	-	-	ns
$t_{RCD}$	$t_{RP}$ parameter	4	3	3	3	2	3	2	CLK
$t_{RP}$	$t_{RCD}$ parameter	4	3	3	3	2	3	2	CLK



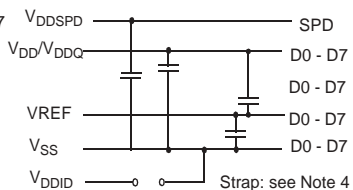
**Part Number Information**



## Block Diagram



BA0 - BA1 → BA0-BA1: DDR SDRAMs D0 - D7  
A0 - A12 → A0-A12: DDR SDRAMs D0 - D7  
RAS → RAS: SDRAMs D0 - D7  
CAS → CAS: SDRAMs D0 - D7  
CKE0 → CKE: SDRAMs D0 - D7  
WE → WE: SDRAMs D0 - D7



## Notes:

1. DQ-to-I/O wiring is shown as recommended but may be changed.
2. DQ/DQS/DM/CKE/CS relationships must be maintained as shown.
3. DQ, DQS, DM/DQS resistors: 22 Ohms.
4. VDDID strap connections (for memory device VDD, VDDQ):  
STRAP OUT (OPEN): VDD = VDDQ  
STRAP IN (VSS): VDD ≠ VDDQ.

**Pin Configurations (Front Side/Back Side)**

Pin	Front	Pin	Front	Pin	Front	Pin	Back	Pin	Back	Pin	Back
1	VREF	67	DQ27	135	DQ34	2	VREF	68	DQ31	136	DQ38
3	VSS	69	VDD	137	VSS	4	VSS	70	VDD	138	VSS
5	DQ0	71	CB0	139	DQ35	6	DQ4	72	CB4	140	DQ39
7	DQ1	73	CB1	141	DQ40	8	DQ5	74	CB5	142	DQ44
9	VDD	75	VSS	143	VDD	10	VDD	76	VSS	144	VDD
11	DQS0	77	DQS8	145	DQ41	12	DM0	78	DM8	146	DQ45
13	DQ2	79	CB2	147	DQS5	14	DQ6	80	CB6	148	DM5
15	VSS	81	VDD	149	VSS	16	VSS	82	VDD	150	VSS
17	DQ3	83	CB3	151	DQ42	18	DQ7	84	CB7	152	DQ46
19	DQ8	85	DU	153	DQ43	20	DQ12	86	DU/(RESET)	154	DQ47
21	VDD	87	VSS	155	VDD	22	VDD	88	VSS	156	VDD
23	DQ9	89	CK2	157	VDD	24	DQ13	90	VSS	158	CK1
25	DQS1	91	CK2	159	VSS	26	DM1	92	VDD	160	CK1
27	VSS	93	VDD	161	VSS	28	VSS	94	VDD	162	VSS
29	DQ10	95	CKE1	163	DQ48	30	DQ14	96	CKE0	164	DQ52
31	DQ11	97	DU(A13)	165	DQ49	32	DQ15	98	DU(BA2)	166	DQ53
33	VDD	99	A12	167	VDD	34	VDD	100	A11	168	VDD
35	CK0	101	A9	169	DQS6	36	VDD	102	A8	170	DM6
37	CK0	103	VSS	171	DQ50	38	VSS	104	VSS	172	DQ54
39	VSS	105	A7	173	VSS	40	VSS	106	A6	174	VSS
Key		107	A5	175	DQ51	Key		108	A4	176	DQ55
41	DQ16	109	A3	177	DQ56	42	DQ20	110	A2	178	DQ60
43	DQ17	111	A1	179	VDD	44	DQ21	112	A0	180	VDD
45	VDD	113	VDD	181	DQ57	46	VDD	114	VDD	182	DQ61
47	DQS2	115	A10/AP	183	DQS7	48	DM2	116	BA1	184	DM7
49	DQ18	117	BA0	185	DQ58	50	DQ22	118	RAS	186	VSS
51	VSS	119	WE	187	DQ58	52	VSS	120	CAS	188	DQ62
53	DQ19	121	S0	189	DQ59	54	DQ23	122	S1	190	DQ63
55	DQ24	123	DU	191	VDD	56	DQ28	124	DU	192	VDD
57	VDD	125	VSS	193	SDA	58	VDD	126	VSS	194	SA0
59	DQ25	127	DQ32	195	SCL	60	DQ29	128	DQ36	196	SA1
61	DQS3	129	DQ33	197	VDDSPD	62	DM3	130	DQ37	198	SA2
63	VSS	131	VDD	199	VDDID	64	VSS	132	VDD	200	DU
65	DQ26	133	DQS4			66	DQ30	134	DM4		

**Notes:**

\* These pins are not used in this module.

**Pin Names**

Pin	Pin Description
A0~A12	Address Input (Multiplexed)
BA0~BA1	Bank Select Address
DQ0~DQ63	Data Input/Output
DQS0~DQS7	Data Strobe Input/Output
CK0~CK2, CK0~CK2,	Clock Input
CKE0	Clock Enable Input
CS0	Chip Select Input
RAS	Row Address Strobe
CAS	Column Address Strobe
WE	Write Enable
DM0~DM7	Data - In Mask

Pin	Pin Description
VDD	Power Supply 2.5V, DDR400 2.6V
VDDQ	Power Supply for DQS2.5V, DDR400 2.6V
VSS	Ground
VREF	Power Supply for Reference
VDDSPD	Serial EEPROM Power Supply (2.3V to 3.6V)
SDA	Serial Data I/O
SCL	Serial Clock
SA0~2	Address in EEPROM
VDDID	VDD Identification Flag
NC	No Connection

# MOSEL VITELIC

V826632G24S

## Serial Presence Detect Information

Bin Sort:

A1 (PC1600 @ CL2)  
B0 (PC2100B @ CL2.5)  
B1 (PC2100A @ CL2)  
C0 (PC2700 @ CL2.5)

D0 (PC3200 @ 2.5-3-3)  
D3 (PC3200 @ 3-3-3 )  
D4 (PC3200 @ 3-4-4)

Byte #	Function described	Function Supported								Hex value							
		A1	B0	B1	C0	D0	D3	D4	A1	B0	B1	C0	D0	D3	D4		
0	Defines # of Bytes written into serial memory at module manufacturer	128bytes								80h							
1	Total # of Bytes of SPD memory device	256bytes								08h							
2	Fundamental memory type	SDRAM DDR								07h							
3	# of row address on this assembly	13								0Dh							
4	# of column address on this assembly	10								0Ah							
5	# of module Rows on this assembly	1 Bank								01h							
6	Data width of this assembly	64 bits								40h							
7	.....Data width of this assembly	-								00h							
8	VDDQ and interface standard of this assembly	SSTL 2.5V								04h							
9	DDR SDRAM cycle time at highest CAS Latency	8ns	7.5ns	7ns	6ns	5ns	5ns	5ns	80h	75h	70h	60h	50h	50h	50h		
10	DDR SDRAM Access time from clock at highest CL	±0.8 ns	±0.75 ns	±0.75 ns	±0.70 ns	±0.65 ns	±0.65 ns	±0.65 ns	80h	75h	75h	70h	65h	65h	65h		
11	DIMM configuration type(Non-parity, Parity, ECC)	Non-parity, ECC								00h							
12	Refresh rate & type	7.8us & Self refresh								82h							
13	Primary DDR SDRAM width	x8								08h							
14	Error checking DDR SDRAM data width	N/A								00h							
15	Minimum clock delay for back-to-back random column address	t <sub>CCD</sub> =1CLK								01h							
16	DDR SDRAM device attributes : Burst lengths supported	2,4,8								0Eh							
17	DDR SDRAM device attributes : # of banks on each DDR SDRAM	4 banks								04h							
18	DDR SDRAM device attributes : CAS Latency supported	2,2.5,3								0Ch	0Ch	0Ch	0Ch	1Ch	1Ch	1Ch	
19	DDR SDRAM device attributes : CS Latency	0CLK								01h							
20	DDR SDRAM device attributes : WE Latency	1CLK								02h							
21	DDR SDRAM module attributes	Differential clock / non Registered								20h							
22	DDR SDRAM device attributes : General	+/-0.2V voltage tolerance								00h							
23	DDR SDRAM cycle time at second highest CL	10ns	10ns	7.5ns	7.5ns	5.0ns	6.0ns	6.0ns	A0h	A0h	75h	75h	50h	60h	60h		

**Serial Presence Detect Information (cont.)**

Byte #	Function described	Function Supported							Hex value						
		A1	B0	B1	C0	D0	D3	D4	A1	B0	B1	C0	D0	D3	D4
24	DDR SDRAM Access time from clock at highest CL	±0.8 ns	±0.75 ns	±0.75 ns	±0.70 ns	±0.65 ns	±0.70 ns	±0.70 ns	80h	75h	75h	70h	65h	70h	70h
25	DDR SDRAM cycle time at third highest CL	-	-	-	-	7.5ns	7.5ns	7.5ns	00h	00h	00h	00h	75h	75h	75h
26	DDR SDRAM Access time from clock at third highest CL	-	-	-	-	±0.75 ns	±0.75 ns	±0.75 ns	00h	00h	00h	00h	75h	75h	75h
27	Minimum row precharge time (=t <sub>RP</sub> )	20ns	20ns	15ns	18ns	15ns	15ns	20ns	50h	50h	3Ch	48h	3Ch	3Ch	50h
28	Minimum row activate to row active delay(=t <sub>RRD</sub> )	15ns	15ns	15ns	12ns	10ns	10ns	10ns	3Ch	3Ch	3Ch	30h	28h	28h	28h
29	Minimum RAS to CAS delay(=t <sub>RCD</sub> )	20ns	20ns	15ns	18ns	15ns	15ns	20ns	50h	50h	3Ch	48h	3Ch	3Ch	50h
30	Minimum active to precharge time(=t <sub>RAS</sub> )	50ns	45ns	45ns	42ns	40ns	40ns	40ns	32h	2Dh	2Dh	2Ah	28h	28h	28h
31	Module ROW density	256MB							40h						
32	Command and address signal input setup time	1.1ns	0.9ns	0.9ns	0.75 ns	0.6ns	0.6ns	0.6ns	B0h	90h	90h	75h	60h	60h	60h
33	Command and address signal input hold time	1.1ns	0.9ns	0.9ns	0.75 ns	0.6ns	0.6ns	0.6ns	B0h	90h	90h	75h	60h	60h	60h
34	Data signal input setup time	0.6ns	0.5ns	0.5ns	0.45 ns	0.4ns	0.4ns	0.4ns	60h	50h	50h	45h	40h	40h	40h
35	Data signal input hold time	0.6ns	0.5ns	0.5ns	0.45 ns	0.4ns	0.4ns	0.4ns	60h	50h	50h	45h	40h	40h	40h
36-40	Superset information (may be used in future)								00h						
41	SDRAM device minimum active to active/auto-refresh time (=t <sub>RC</sub> )	70ns	65ns	65ns	60ns	60ns	60ns	60ns	46h	41h	41h	3Ch	3Ch	3Ch	3Ch
42	SDRAM device minimum active to autorefresh to active/auto-refresh time (=t <sub>RFC</sub> )	80ns	75ns	75ns	72ns	70ns	70ns	70ns	50h	4Bh	4Bh	48h	46h	46h	46h
43	SDRAM device maximum device cycle time (=t <sub>CK MAX</sub> )	12ns	12ns	12ns	12ns	12ns	12ns	12ns	30h	30h	30h	30h	30h	30h	30h
44	SDRAM device maximum skew between DQS and DQ signals (=t <sub>DQSQ</sub> )	0.6ns	0.5ns	0.5ns	0.45 ns	0.4ns	0.4ns	0.4ns	3Ch	32h	32h	2Dh	28h	28h	28h
45	SDRAM device maximum read datahold skew factor (=t <sub>QHS</sub> )	1ns	0.75 ns	0.75 ns	0.60 ns	0.55 ns	0.55 ns	0.55 ns	A0h	75h	75h	60h	55h	55h	55h
46-61	Superset information (may be used in future)	-							00h						
62	SPD data revision code	Initial release							00h	00h	00h	00h	11h	11h	11h
63	Checksum for Bytes 0 ~ 62	-							E7h	22h	CAh	4Bh	A3h	BEh	E6h
64	Manufacturer JEDEC ID code	Mosel Vitelic							40h						

Byte #	Function described	Function Supported							Hex value						
		A1	B0	B1	C0	D0	D3	D4	A1	B0	B1	C0	D0	D3	D4
65 - 71	..... Manufacturer JEDEC ID code								00h						
72	Manufacturing location	02=Taiwan 05=China 0A=S-CH													
73-90	Module part number (ASCII)	V826632G24S													
91	Manufacturer revision code (For PCB)	0							00						
92	Manufacturer revision code (For component)	0							00						
93	Manufacturing date (Week)	-							-						
94	Manufacturing date (Year)	-							-						
95~98	Assembly serial #	-							-						
99~127	Manufacturer specific data (may be used in future)	Undefined							00h						
128~255	Open for customer use	Undefined							00h						

### DC Operating Conditions

(T<sub>A</sub> = 0 to 70°C, Voltage referenced to V<sub>SS</sub> = 0V)

Parameter	Symbol	Min	Typ.	Max	Unit	Note
Power Supply Voltage	V <sub>DD</sub>	2.3	2.5	2.7	V	
Power Supply Voltage for DDR400	V <sub>DD</sub>	2.5	2.6	2.7	V	
Power Supply Voltage	V <sub>DDQ</sub>	2.3	2.5	2.7	V	1
Power Supply Voltage for DDR400	V <sub>DDQ</sub>	2.5	2.6	2.7	V	1
Input High Voltage	V <sub>IH</sub>	V <sub>REF</sub> + 0.15	-	V <sub>DDQ</sub> + 0.3	V	
Input Low Voltage	V <sub>IL</sub>	-0.3	-	V <sub>REF</sub> - 0.15	V	2
I/O Termination Voltage	V <sub>TT</sub>	V <sub>REF</sub> - 0.04	V <sub>REF</sub>	V <sub>REF</sub> + 0.04	V	
Reference Voltage	V <sub>REF</sub>	V <sub>DDQ/2</sub> - 0.05	-	V <sub>DDQ/2</sub> + 0.05	V	
Input Leakage Current	I <sub>I</sub>	-2	-	2	μA	
Output Leakage Current	I <sub>OZ</sub>	-5	-	5	μA	
Output High Current (V <sub>OUT</sub> = 1.95V)	I <sub>OH</sub>	-16.8	-	-	mA	
Output Low Current (V <sub>OUT</sub> = 0.35V)	I <sub>OL</sub>	16.8	-	-	mA	

**Notes:** 1. V<sub>DDQ</sub> must not exceed the level of V<sub>DD</sub>.  
 2. V<sub>IL</sub> (min) is acceptable -1.5V AC pulse width with <=5ns of duration.  
 3. The value of V<sub>REF</sub> is approximately equal to 0.5V<sub>DDQ</sub>.

**AC Operating Conditions**(T<sub>A</sub> = 0 to 70 °C, Voltage referenced to V<sub>SS</sub> = 0V)

Parameter	Symbol	Min	Max	Unit	Note
Input High (Logic 1) Voltage, DQ, DQS and DM signals	V <sub>IH(AC)</sub>	V <sub>REF</sub> + 0.31		V	
Input Low (Logic 0) Voltage, DQ, DQS and DM signals	V <sub>IL(AC)</sub>		V <sub>REF</sub> - 0.31	V	
Input Differential Voltage, CK and $\overline{\text{CK}}$ inputs	V <sub>ID(AC)</sub>	0.7	V <sub>DDQ</sub> + 0.6	V	1
Input Crossing Point Voltage, CK and $\overline{\text{CK}}$ inputs	V <sub>IX(AC)</sub>	0.5*V <sub>DDQ-0.2</sub>	0.5*V <sub>DDQ+0.2</sub>	V	2

**Notes:** 1. VID is the magnitude of the difference between the input level on CK and the input on  $\overline{\text{CK}}$ .  
 2. The value of VIX is expected to equal 0.5\*V<sub>DDQ</sub> of the transmitting device and must track variations in the DC level of the same.

**AC Operating Test Conditions** (T<sub>A</sub> = 0 to 70°C, Voltage referenced to V<sub>SS</sub> = 0V)

Parameter	Value	Unit
Reference Voltage	V <sub>DDQ</sub> × 0.5	V
Termination Voltage	V <sub>DDQ</sub> × 0.5	V
AC Input High Level Voltage (V <sub>IH</sub> , min)	V <sub>REF</sub> + 0.31	V
AC Input Low Level Voltage (V <sub>IL</sub> , max)	V <sub>REF</sub> - 0.31	V
Input Timing Measurement Reference Level Voltage	V <sub>REF</sub>	V
Output Timing Measurement Reference Level Voltage	V <sub>TT</sub>	V
Input Signal maximum peak swing	1.5	V
Input minimum Signal Slew Rate	1	V/ns
Termination Resistor (R <sub>T</sub> )	50	Ohm
Series Resistor (R <sub>S</sub> )	25	Ohm
Output Load Capacitance for Access Time Measurement (C <sub>L</sub> )	30	pF



**DDR SDRAM  $I_{DD}$  SPEC TABLE**

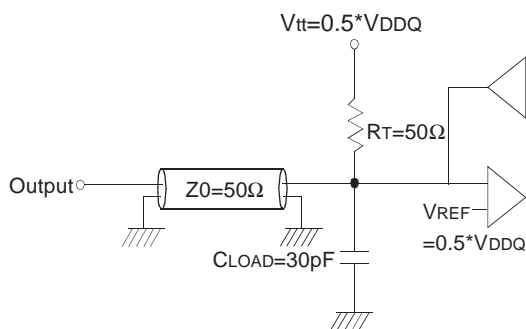
Symbol		A1 PC1600 CL=2	B0 PC2100B CL=2.5	B1 PC2100A CL=2	C0 PC2700A CL=2.5	D0/D3/D4 PC3200 CL=3	Unit
IDD0		720	800	800	880	960	mA
IDD1		800	960	960	1120	1280	mA
IDD2P		60	60	60	60	60	mA
IDD2F		200	250	250	280	330	mA
IDD2Q		130	170	170	190	220	mA
IDD3P		240	260	260	300	340	mA
IDD3N		360	380	380	480	580	mA
IDD4R		1200	1520	1520	1840	2160	mA
IDD4W		1040	1360	1360	1680	2000	mA
IDD5		1440	1520	1520	1600	1680	mA
IDD6	Normal	48	48	48	48	48	mA
	Low power	29	29	29	29	29	mA
IDD7		2000	2400	2400	2800	3200	mA

\* Module  $I_{DD}$  was calculated on the basis of component  $I_{DD}$  and can be differently measured according to DQ loading cap.

**Detailed test conditions for DDR SDRAM IDD1 & IDD****IDD1 : Operating current: One bank operation**

1. Typical Case :  $V_{dd} = 2.5V$ ,  $T = 25^{\circ}C$
2. Worst Case :  $V_{dd} = 2.7V$ ,  $T = 10^{\circ}C$
3. Only one bank is accessed with  $t_{RC}(\min)$ , Burst Mode, Address and Control inputs on NOP edge are changing once per clock cycle.  $I_{out} = 0mA$
4. Timing patterns
  - DDR200(100Mhz, CL=2) :  $t_{CK} = 10ns$ , CL2, BL=4,  $t_{RCD} = 2 \cdot t_{CK}$ ,  $t_{RAS} = 5 \cdot t_{CK}$   
Read : A0 N R0 N N P0 N A0 N - repeat the same timing with random address changing  
\*50% of data changing at every burst
  - DDR266B(133Mhz, CL=2.5) :  $t_{CK} = 7.5ns$ , CL=2.5, BL=4,  $t_{RCD} = 3 \cdot t_{CK}$ ,  $t_{RC} = 9 \cdot t_{CK}$ ,  $t_{RAS} = 5 \cdot t_{CK}$   
Read : A0 N N R0 N P0 N N A0 N - repeat the same timing with random address changing  
\*50% of data changing at every burst
  - DDR266A (133Mhz, CL=2) :  $t_{CK} = 7.5ns$ , CL=2, BL=4,  $t_{RCD} = 3 \cdot t_{CK}$ ,  $t_{RC} = 9 \cdot t_{CK}$ ,  $t_{RAS} = 5 \cdot t_{CK}$   
Read : A0 N N R0 N P0 N N A0 N - repeat the same timing with random address changing  
\*50% of data changing at every burst

Legend : A=Activate, R=Read, W=Write, P=Precharge, N=NOP



Output Load Circuit (SSTL\_2)

**Input/Output Capacitance**(V<sub>DD</sub> = 2.5V, V<sub>DD</sub> = 2.6V, V<sub>DDQ</sub> = 2.5V, V<sub>DDQ</sub> = 2.6V, T<sub>A</sub> = 25°C, f = 1MHz)

Parameter	Symbol	Min	Max	Unit
Input capacitance (A <sub>0</sub> ~ A <sub>11</sub> , BA <sub>0</sub> ~ BA <sub>1</sub> , $\overline{\text{RAS}}$ , $\overline{\text{CAS}}$ , $\overline{\text{WE}}$ )	CIN <sub>1</sub>	36	45	pF
Input capacitance (CKE <sub>0</sub> )	CIN <sub>2</sub>	36	45	pF
Input capacitance ( $\overline{\text{CS}}$ <sub>0</sub> )	CIN <sub>3</sub>	34	42	pF
Input capacitance (CLK <sub>1</sub> , CLK <sub>2</sub> )	CIN <sub>4</sub>	34	38	pF
Data & DQS input/output capacitance (DQ <sub>0</sub> ~DQ <sub>63</sub> )	C <sub>OUT</sub>	8	9	pF
Input capacitance (DM0~DM8)	CIN <sub>5</sub>	8	9	pF

**AC Characteristics** (AC operating conditions unless otherwise noted)

Parameter	Sym- bol	(DDR400A) D0		(DDR400B) D3		(DDR400C) D4		(DDR333) C0		(DDR266A) B1		(DDR266B) B0		(DDR200) A1		Unit	Note
		Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	Min	Max		
Row Cycle Time	t <sub>RC</sub>	60	-	60	-	60	-	60	-	65	-	65	-	70	-	ns	
Auto Refresh Row Cycle Time	t <sub>RFC</sub>	70	-	70	-	70	-	72	-	75	-	75	-	80	-	ns	
Row Active Time	t <sub>RAS</sub>	40	120K	40	120K	40	120K	42	120K	45	120K	45	120K	50	120K	ns	
Row Address to Column Address Delay	t <sub>RCD</sub>	15	-	15	-	20	-	18	-	15	-	20	-	20	-	ns	
Row Active to Row Active Delay	t <sub>RRD</sub>	10	-	10	-	10	-	12	-	15	-	15	-	15	-	ns	
Column Address to Column Address Delay	t <sub>CCD</sub>	1	-	1	-	1	-	1	-	1	-	1	-	1	-	CLK	
Row Precharge Time	t <sub>RP</sub>	15	-	15	-	20	-	18	-	15	-	20	-	20	-	ns	
Write Recovery Time	t <sub>WR</sub>	15	-	15	-	15	-	12	-	15	-	15	-	15	-	ns	
Last Data-In to Read Command	t <sub>DRL</sub>	1	-	1	-	1	-	1	-	1	-	1	-	1	-	CLK	

## AC Characteristics (cont.)

Parameter	Sym- bol	(DDR400A) D0		(DDR400B) D3		(DDR400C) D4		(DDR333) C0		(DDR266A) B1		(DDR266B) B0		(DDR200) A1		Unit	Note
		Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	Min	Max		
Auto Precharge Write Recovery + Precharge Time	$t_{DAL}$	35	-	35	-	35	-	35	-	35	-	35	-	35	-	ns	
System Clock Cycle Time	$\overline{CAS}$ Latency = 3	$t_{CK}$	5	12	5	12	5	12	-	12	-	12	-	12	-	12	ns
	$\overline{CAS}$ Latency = 2.5		5	12	6	12	6	12	6	12	7	12	7.5	12	8	12	ns
	$\overline{CAS}$ Latency = 2		7.5	12	7.5	12	7.5	12	7.5	12	7.5	12	10	12	10	12	ns
Clock High Level Width	$t_{CH}$	0.45	0.55	0.45	0.55	0.45	0.55	0.45	0.55	0.45	0.55	0.45	0.55	0.45	0.55	CLK	
Clock Low Level Width	$t_{CL}$	0.45	0.55	0.45	0.55	0.45	0.55	0.45	0.55	0.45	0.55	0.45	0.55	0.45	0.55	CLK	
Data-Out edge to Clock edge Skew	$t_{AC}$	-0.65	0.65	-0.65	0.65	-0.65	0.65	-0.75	0.75	-0.75	0.75	-0.75	0.75	-0.8	0.8	ns	
DQS-Out edge to Clock edge Skew	$t_{DQSK}$	-0.60	0.60	-0.60	0.60	-0.60	0.60	-0.75	0.75	-0.75	0.75	-0.75	0.75	-0.8	0.8	ns	
DQS-Out edge to Data-Out edge Skew	$t_{DQSQ}$	-	0.40	-	0.40	-	0.40	-	0.45	-	0.5	-	0.5	-	0.6	ns	
Data-Out hold time from DQS	$t_{QH}$	$t_{HPmin}$ - 0.75ns	-	$t_{HPmin}$ - 0.75ns	-	$t_{HPmin}$ - 0.75ns	-	$t_{HPmin}$ - 0.75ns	-	$t_{HPmin}$ - 0.75ns	-	$t_{HPmin}$ - 0.75ns	-	$t_{HPmin}$ - 0.75ns	-	ns	1
Clock Half Period	$t_{HP}$	$t_{CH/L}$ min	-	$t_{CH/L}$ min	-	$t_{CH/L}$ min	-	$t_{CH/L}$ min	-	$t_{CH/L}$ min	-	$t_{CH/L}$ min	-	$t_{CH/L}$ min	-	ns	1
Input Setup Time (fast slew rate)	$t_{IS}$	0.6	-	0.6	-	0.6	-	0.75	-	0.9	-	0.9	-	1.1	-	ns	2,3,5,6
Input Hold Time (fast slew rate)	$t_{IH}$	0.6	-	0.6	-	0.6	-	0.75	-	0.9	-	0.9	-	1.1	-	ns	2,3,5,6
Input Setup Time (slow slew rate)	$t_{IS}$	0.75	-	0.75	-	0.75	-	0.8	-	1.0	-	1.0	-	1.1	-	ns	2,4,5,6
Input Hold Time (slow slew rate)	$t_{IH}$	0.75	-	0.75	-	0.75	-	0.8	-	1.0	-	1.0	-	1.1	-	ns	2,4,5,6
Input Pulse Width	$t_{IPW}$	0.4	0.6	0.4	0.6	0.4	0.6	0.4	0.6	2.2	-	2.2	-	-	-	ns	6
Write DQS High Level Width	$t_{DQSH}$	0.35		0.35		0.35		0.35		0.35		0.35		0.35		CLK	
Write DQS Low Level Width	$t_{DQSL}$	0.35		0.35		0.35		0.35		0.35		0.35		0.35		CLK	
CLK to First Rising edge of DQS-In	$t_{DQSS}$	0.72	1.25	0.72	1.25	0.72	1.25	0.75	1.25	0.75	1.25	0.75	1.25	0.75	1.25	CLK	

Parameter	Sym- bol	(DDR400A) D0		(DDR400B) D3		(DDR400C) D4		(DDR333) C0		(DDR266A) B1		(DDR266B) B0		(DDR200) A1		Unit	Note
		Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	Min	Max		
Data-In Setup Time to DQS-In (DQ & DM)	$t_{DS}$	0.40	-	0.40	-	0.40	-	0.45	-	0.5	-	0.5	-	0.6	-	ns	7
Data-in Hold Time to DQS-In (DQ & DM)	$t_{DH}$	0.40	-	0.40	-	0.40	-	0.45	-	0.5	-	0.5	-	0.6	-	ns	7
DQ & DM Input Pulse Width	$t_{DIPW}$	1.75	-	1.75	-	1.75	-	1.75	-	1.75	-	1.75	-	2	-	ns	
Read DQS Preamble Time	$t_{RPRE}$	0.9	1.1	0.9	1.1	0.9	1.1	0.9	1.1	0.9	1.1	0.9	1.1	0.9	1.1	CLK	
Read DQS Postamble Time	$t_{RPST}$	0.4	0.6	0.4	0.6	0.4	0.6	0.4	0.6	0.4	0.6	0.4	0.6	0.4	0.6	CLK	
Write DQS Preamble Setup Time	$t_{WPRES}$	0	-	0	-	0	-	0	-	0	-	0	-	0	-	CLK	
Write DQS Preamble Hold Time	$t_{WPREH}$	0.25	-	0.25	-	0.25	-	0.25	-	0.25	-	0.25	-	0.25	-	CLK	
Write DQS Postamble Time	$t_{WPST}$	0.4	0.6	0.4	0.6	0.4	0.6	0.4	0.6	0.4	0.6	0.4	0.6	0.4	0.6	CLK	
Mode Register Set Delay	$t_{MRD}$	2	-	2	-	2	-	2	-	2	-	2	-	2	-	CLK	
Power Down Exit Time to any command	$t_{XPDN}$	1	-	1	-	1	-	1	-	1	-	1	-	1	-	CLK	
Exit Self Refresh to Non-Read Command	$t_{XSNR}$	200	-	200	-	200	-	200	-	75	-	75	-	80	-	CLK	
Exit Self Refresh to Read Command	$t_{XSRD}$	200	-	200	-	200	-	200	-	200	-	200	-	200	-	CLK	8
Average Periodic Refresh Interval	$t_{REFI}$	-	7.8	-	7.8	-	7.8	-	7.8	-	7.8	-	7.8	-	7.8	us	

- Notes:**
1. This calculation accounts for  $t_{DQSQ(max)}$ , the pulse width distortion of on-chip circuit and jitter.
  2. Data sampled at the rising edges of the clock : A0~A11, BA0~BA1, CKE,  $\overline{CS}$ , RAS,  $\overline{CAS}$ ,  $\overline{WE}$ .
  3. For command/address input slew rate  $\geq 1.0V/ns$
  4. For command/address input slew rate  $\geq 0.5V/ns$  and  $< 1.0V/ns$
  5. CK,  $\overline{CK}$  slew rates are  $\geq 1.0V/ns$
  6. These parameters guarantee device timing, but they are not necessarily tested on each device, and they may be guaranteed by design or tester correlation.
  7. Data latched at both rising and falling edges of Data Strobes(DQS) : DQ, DM
  8. Minimum of 200 cycles of stable input clocks after Self Refresh Exit command, where CKE is held high, is required to complete Self Refresh Exit and lock the internal DLL circuit of DDR SDRAM.

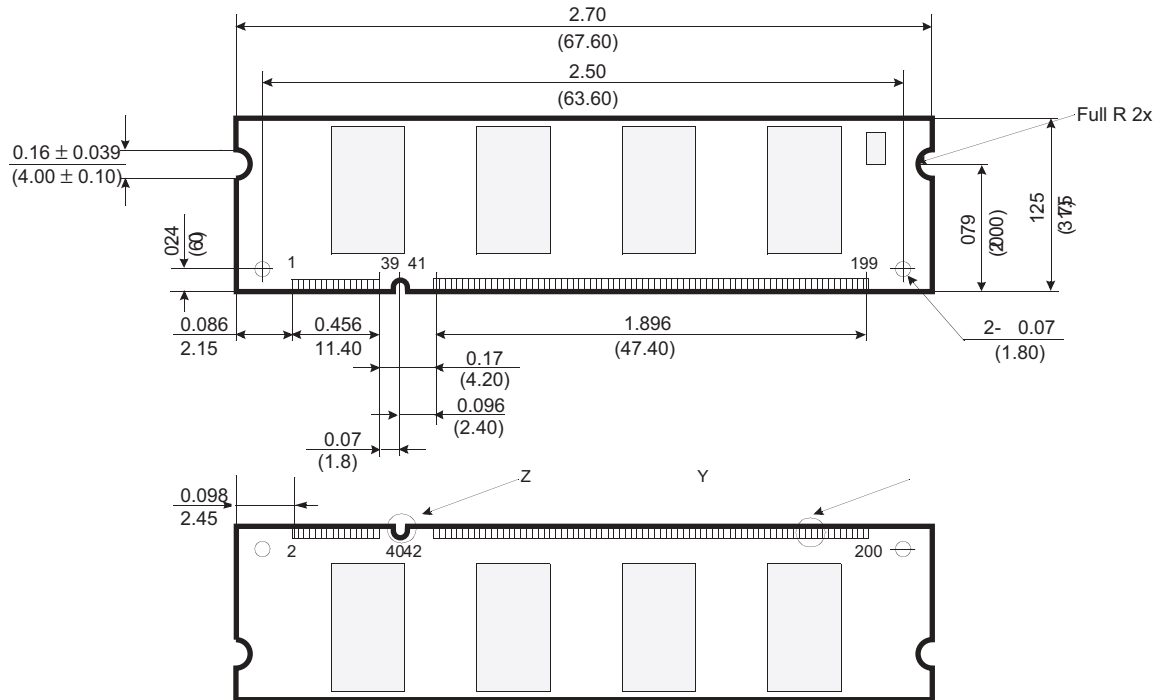
### Absolute Maximum Ratings

Parameter	Symbol	Rating	Unit
Ambient Temperature	$T_A$	0 ~ 70	°C
Storage Temperature	$T_{STG}$	-55 ~ 125	°C
Voltage on Any Pin relative to $V_{SS}$	$V_{IN}, V_{OUT}$	-0.5 ~ 3.6	V
Voltage on $V_{DD}$ relative to $V_{SS}$	$V_{DD}$	-0.5 ~ 3.6	V
Voltage on $V_{DDQ}$ relative to $V_{SS}$	$V_{DDQ}$	-0.5 ~ 3.6	V
Output Short Circuit Current	$I_{OS}$	50	mA
Power Dissipation	$P_D$	6	W
Soldering Temperature • Time	$T_{SOLDER}$	260 • 10	°C • Sec

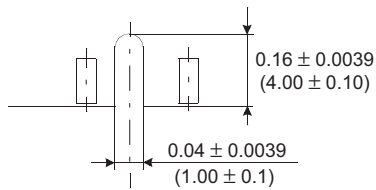
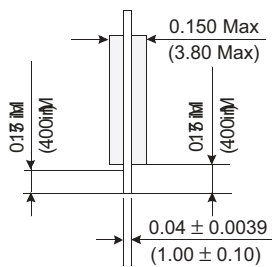
**Note:** Operation at above absolute maximum rating can adversely affect device reliability

**Package Dimensions**

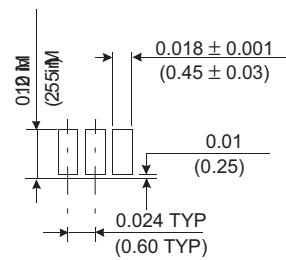
Units : Inches (Millimeters)



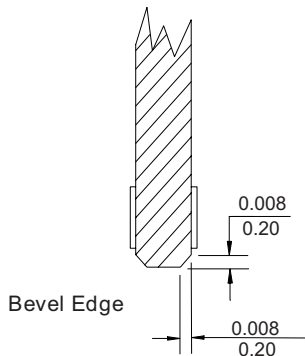
Tolerances :  $\pm 0.006$  (.15) unless otherwise specified



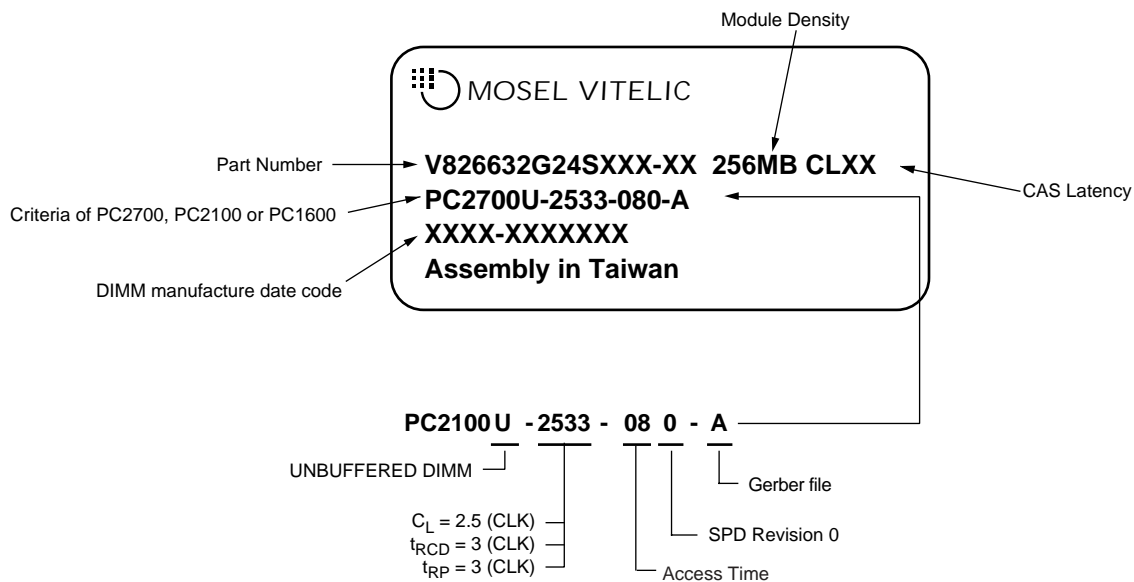
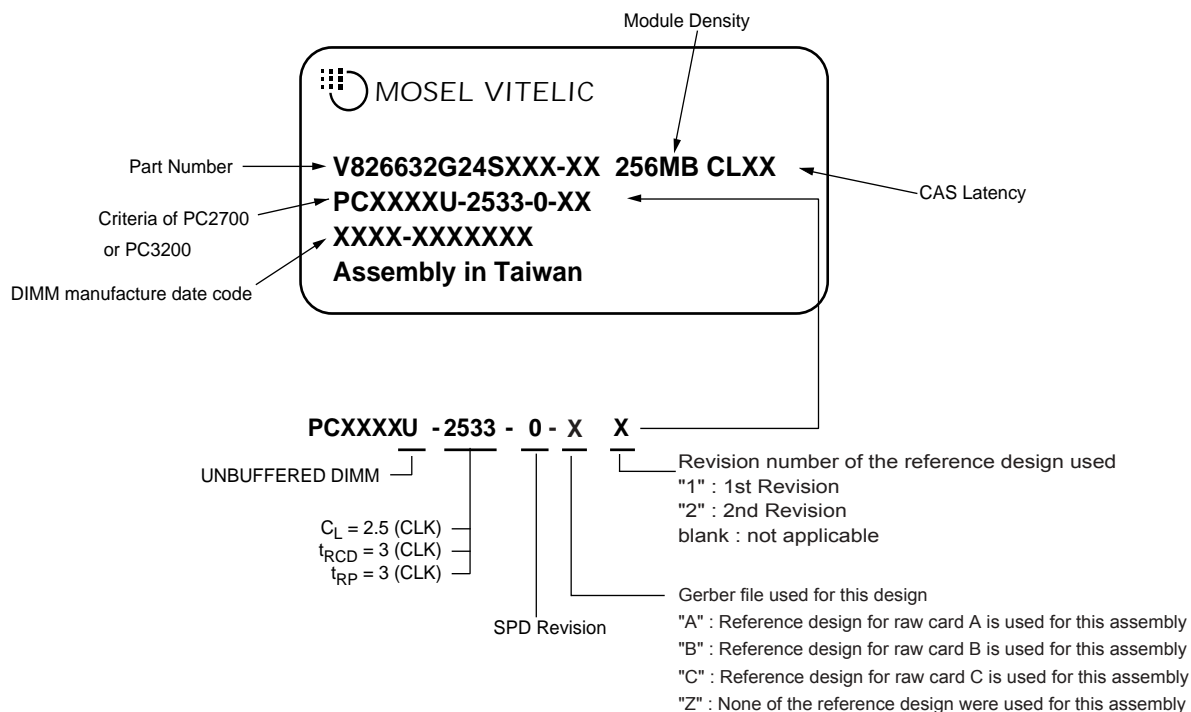
Detail Z



Detail Y



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